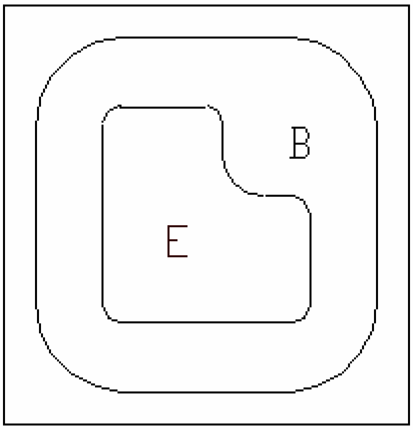
9014B Silicon NPN Epitaxial Transistor

Description :The 9014B is designed for use in pre-amplifier of low level and low noise

Features: ●Excellent h_{FE} Linearity

●Complementary to 9015B

Chip Appearance

	Chip Size		350um×350um
	Chip Thickness		210±20um
	Bonding Pad Size	Base	110um×110um
		Emitter	100um×100um
	Front Metal		Al
	Backside Metal		Au(As)
	Scribe line width		40um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25℃)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}=40V, I_E=0		0.1	uA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0		0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=0.1mA,	50		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA,	45		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=0.1mA,	5.0		V
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=1mA	150	600	
Collector Saturation Voltage	$V_{CE(sat)}$	I_C=100mA,I_B=5mA		0.30	V